

DV01 SERIES LOTO DIAPHRAGM VALVE

GENTEC® DV01 Series LOTO Diaphragm Valve is developed for use with integrated gas systems (IGS).



SLVV-DV01M-11C2-W-S1



SLVV-DV01M-11C2-B-S1

Features

- Assembled and packaged for Ultra-high purity semiconductor applications
- Compact Design
- LOTO Handle (Lock-out-tag-out handle)
- Cobalt-based superalloy diaphragm
- 100% Helium-leak tested
- 1.125" C-Seal or 1.125" W-Seal

Materials

- Body: 316L VIM VAR, 316L VAR
- Seat: PCTFE
- Diaphragm: Co-Ni Super Alloy

Specifications

- Flow capacity: Cv=0.2
- Maximum leak Rate:
Inboard leakage: 3×10^{-11} atm cc/sec He
Across seat leakage: 1×10^{-9} atm cc/sec He

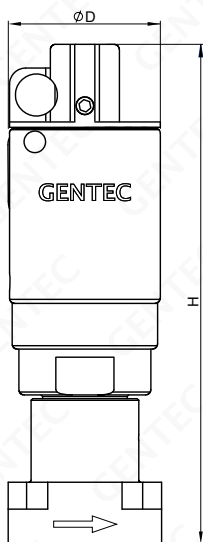
Operating Conditions

- Maximum Operating Pressure: 150 psi
- Minimum Operating Pressure: vacuum
- Temperature: $-10^{\circ}\text{C} \sim 80^{\circ}\text{C}$ ($14^{\circ}\text{F} \sim 176^{\circ}\text{F}$)

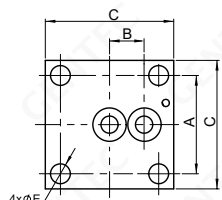
Wetted Surface

- Ra: 5 μin
- Wetted Components processed according to GENTEC Ultra High Purity Process Specification (GC-S1)

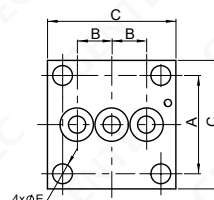
Dimensions



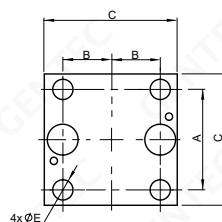
Manual (LOTO)



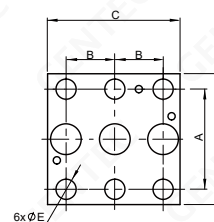
C-Seal (two holes)



C-Seal (three holes)



W-Seal (two holes)

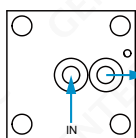


W-Seal (three holes)

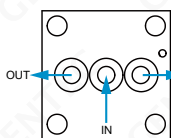
Dimensions: in. (mm)

Actuation	Dimensions					
	A	B	C	D	E	H
Manual (W-Seal)	0.86" (21.8)	0.39" (10.0)	1.12" (28.5)	1.10" (28.0)	0.17" (4.4)	3.65" (92.8)
Manual (C-Seal)	0.86" (21.8)	0.31" (7.75)	1.12" (28.5)	1.10" (28.0)	0.17" (4.4)	3.65" (92.8)

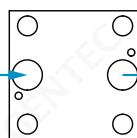
Inlet and Outlet



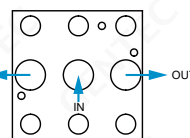
C-Seal (two holes)



C-Seal (three holes)



W-Seal (two holes)



C-Seal (three holes)

Ordering Information

Ex:	SLVV	- DV01	M -	- 11C2	- W	- S1
	Body	Series Number	Actuation	Connection Type	Knob Color	Process Standard
	SLVV: 316L VIM VAR SLV: 316L VAR	DV01	M: Manual	11C2: 1.125" C-Seal, two holes 11C3: 1.125" C-Seal, three holes 11W2: 1.125" W-Seal, two holes 11W3: 1.125" W-Seal, three holes Other connection styles are available	W: Anodized Natural Color B: Anodized Blue R: Anodized Red Blank: Anodized Black	S1: Ultra-high purity process